

30V N-Channel PowerTrench[®] MOSFET

General Description

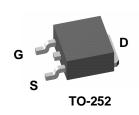
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

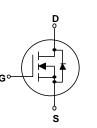
Applications

DC/DC converter

Features

- 65 A, 30 V. $R_{DS(ON)} = 9.5 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$ $R_{DS(ON)} = 8 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$
- High performance trench technology for extremely low $R_{\text{DS}(\text{ON})}$
- Low gate charge (33 nC typical)
- High power and current handling capability





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units	
V _{DSS}	Drain-Source Voltage		30	V	
V _{GSS}	Gate-Source Voltage		±12	V	
I _D	Drain Current – Continuous	(Note 1a)	65	A	
	– Pulsed		100		
P _D	Maximum Power Dissipation @ $T_c = 25^{\circ}C$ (Note 1)		70	W	
	@ T _A = 25°C	(Note 1a)	3.2		
	@ T _A = 25°C	(Note 1b)	1.3		
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C	

Thermal Characteristics

R _{θJC}	Thermal Resistance, Junction-to-Case	(Note 1)	1.8	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1b)	96	°C/W

Package Marking and Ordering Information

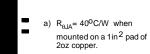
FDD6672A FDD6672A 13" 16mm 2500 units	Device Marking	Device	Reel Size	Tape width	Quantity
	FDD6672A	FDD6672A	13"	16mm	2500 units

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	cal Characteristics	$T_A = 25^{\circ}C$ unless otherwise noted	1			
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics		•		•	•
BV _{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0 V, I_D = 250 \mu A$	30			V
ΔBV_{DSS} ΔT_J	Breakdown Voltage Temperature Coefficient	I_{D} = 250 µA, Referenced to 25°C		20		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 V, V_{GS} = 0 V$			1	μA
	Gate-Body Leakage, Forward	$V_{GS} = 12 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
	Gate-Body Leakage, Reverse	$V_{GS} = -12 V V_{DS} = 0 V$			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	0.8	1.2	2.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu$ A, Referenced to 25° C		-4		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = 4.5 \text{ V}, \text{ I}_D = 13 \text{ A}$ $V_{GS} = 4.5 \text{ V}, \text{ I}_D = 13 \text{ A}, \text{ T}_J = 125^{\circ}\text{C}$ $V_{GS} = 10 \text{ V}, \text{ I}_D = 14 \text{ A}$		8.2 11.5 6.8	9.5 16 8	mΩ
D(on)	On-State Drain Current		50			Α
g _{FS}	Forward Transconductance	$V_{DS} = 10 \text{ V}, \qquad I_{D} = 15 \text{ A}$		75		S
Dynamic	Characteristics	·				
C _{iss}	Input Capacitance	$V_{DS} = 15 V, V_{GS} = 0 V,$		5070		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		550		pF
C _{rss}	Reverse Transfer Capacitance			230		pF
Switchir	g Characteristics (Note 2)					
t _{d(on)}	Turn–On Delay Time	$V_{DD} = 10 \text{ V}, I_D = 1 \text{ A},$		17	25	ns
t _r	Turn–On Rise Time	69 10		25	ns	
t _{d(off)}	Turn–Off Delay Time			100	ns	
t _f	Turn–Off Fall Time			29	42	ns
Q _g	Total Gate Charge	$V_{DS} = 15 V, I_D = 15 A,$ 33 46		nC		
Q _{gs}	Gate-Source Charge	$V_{GS} = 4.5 V$ 7.5			nC	
Q _{gd}	Gate-Drain Charge			6.8		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
ls	Maximum Continuous Drain-Source				2.7	Α
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V$, $I_{S} = 2.7 A$ (Note 2)		0.7	1.2	V

Notes:

1. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the drain tab. R_{BJC} is guaranteed by design while R_{BCA} is determined by the user's board design.

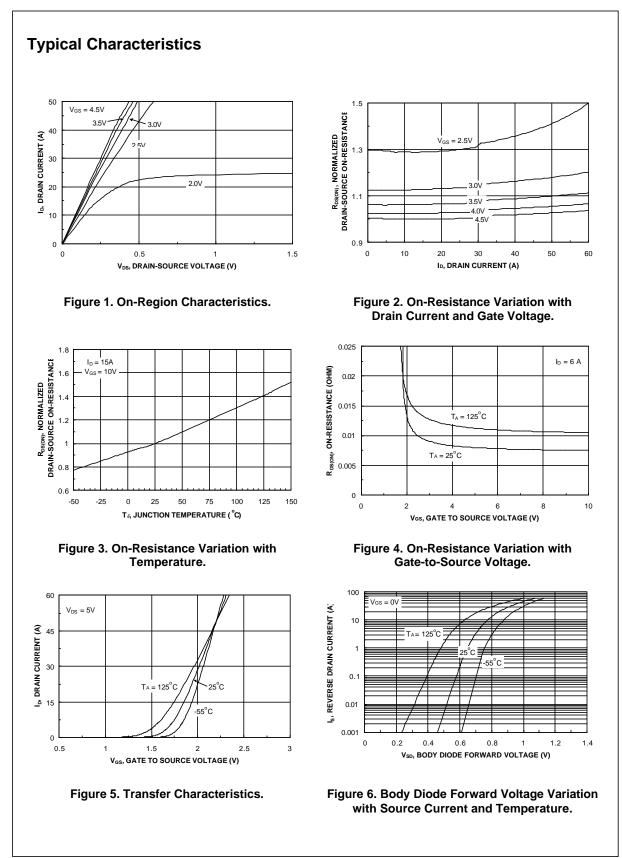


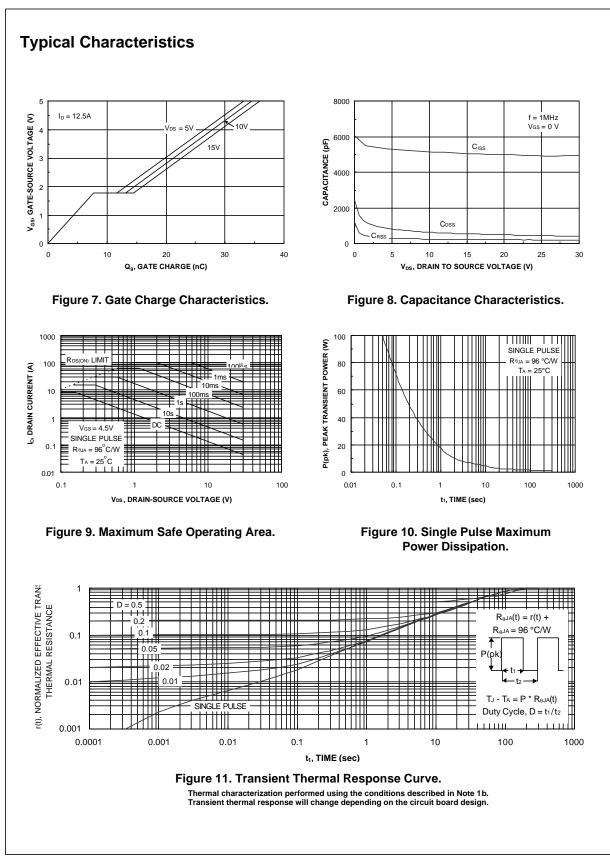


b) $R_{\theta JA}$ = 96^oC/W on a minimum mounting pad.

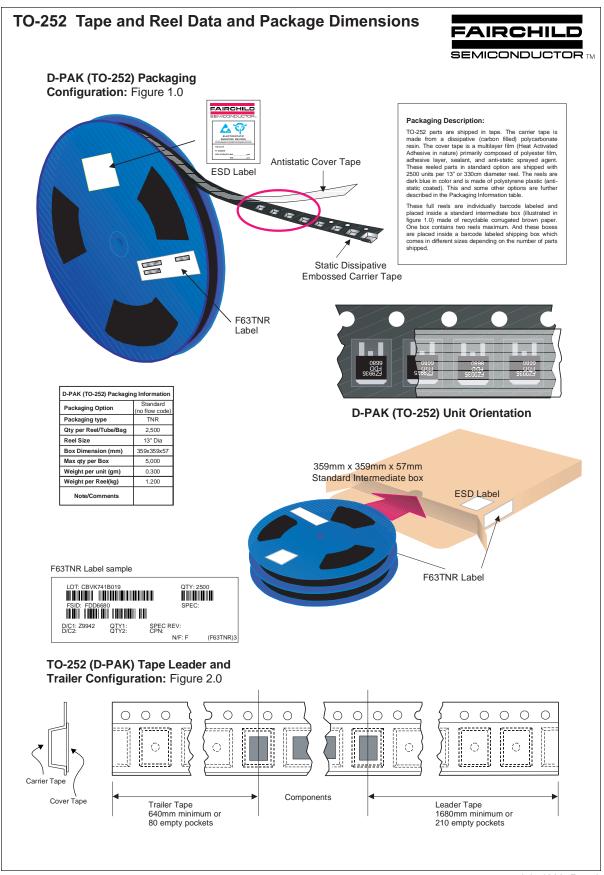
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 $\mu s,$ Duty Cycle < 2.0%

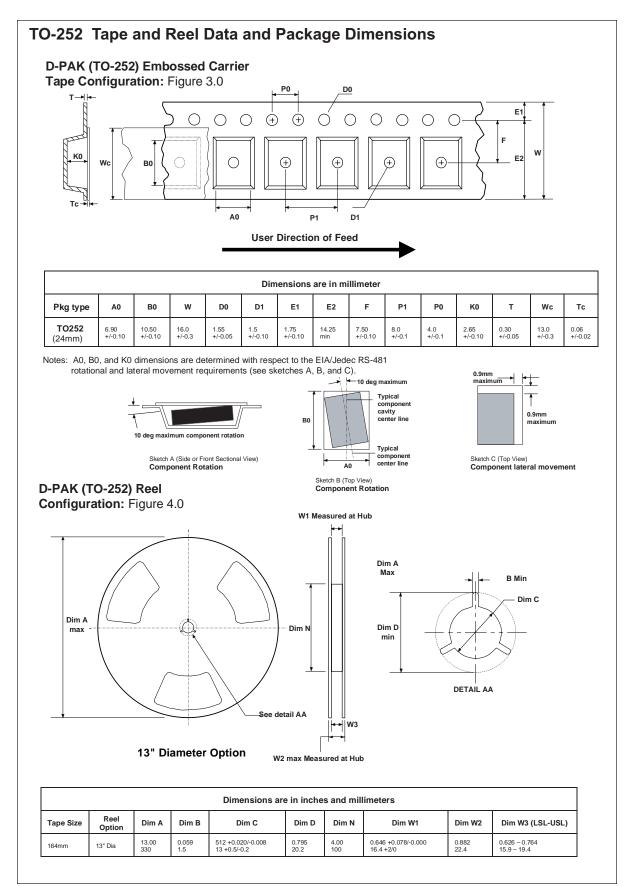


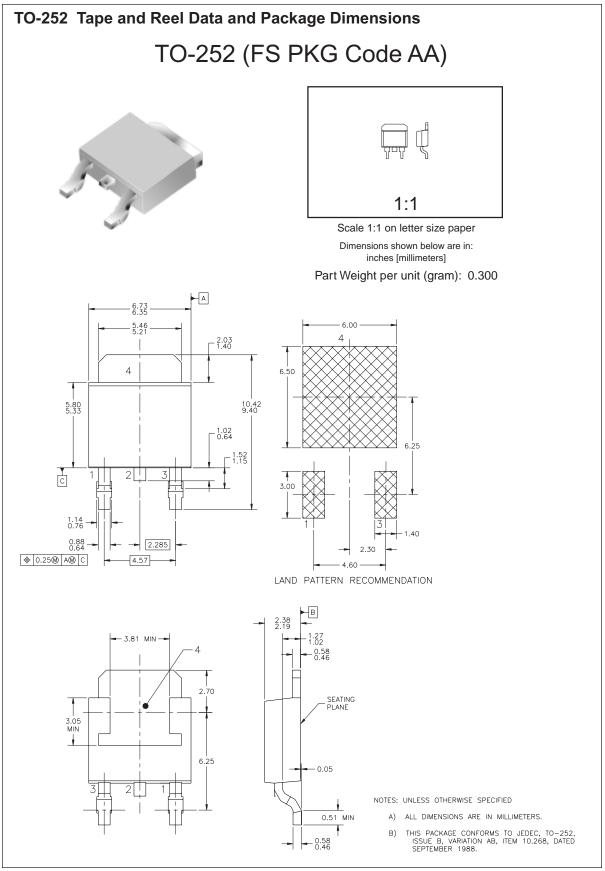


FDD6672A Rev B(W)



July 1999, Rev. A





September 1999, Rev. A

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